

FOR USE BY ELECTRICIANS OVERSEAS :

最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 (T _b =25°C)					電気的特性 (T _b =25°C)										外形	備考
				V _{ceo} (V)	V _{ceo} (V)	I _c (mA)	P _c (mW)	T _j (°C)	I _{ceo} 最大値 (μA)	直流又はパルスI _{BE}		バイアス		h _{FE}	h _{FE} h _{FE} * (Ω)	h _{FE} h _{FE} * (×10 ⁻⁴)	h _{FE} h _{FE} * (μS)	f _{αB} f _r * (Mc)		
1	2	3	4	5					6		7		8				9	10	11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{CBO} MAXIMUM VALUE AND V_{CB} VALUE (CRITERIA FOR MEASURING I_{CBO})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{CE}, I_C (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{CB}, I_E (CRITERIA FOR MEASURING h PARAMETERS)

- * INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
 - 9 f_{αB} OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_r.
 - 10 C_{ob} AND r_{bb'} OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN r_{bb'} COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
 - 11 OUTLINE
 - 12 REMARKS
- :とコンプリ: COMPLEMENTARY TO

型名	社名	用途	構造	最大定格 (T _a = 25°C)					電 気 的 特 性 (T _a = 25°C)											外 形	備 考						
				V _{CB0} (V)	V _{EB0} (V)	I _C (mA)	P _C (mW)	T _J (°C)	I _{CB0} 最大値		直流又はパルス hFE		バ イ ア ス		h _{fe}	h _{ic} h _{ib} * (Ω)	h _{re} h _{rb} * (×10 ⁻⁴)	h _{oe} h _{ob} * (μU)	f _{ab} f _T * (Mc)			C _{ob} (pF)	r _{bb} h _{ie(rea)} * (Ω)				
									V _{CE} (V)	I _C (mA)	V _{CE} (V)	I _E (mA)	V _{CE} (V)	I _E (mA)										h _{fb} *	h _{fb} *		
★ 2SA511	東 芝	PA	Si, TP	-90	-5	-1A	800	150	-1	-30																2SC511 ヒコンプリ	
" 512	"	PA, SW	Si, E	-80	-5	-1.5A	800	175	-1	-30	30~150	-2	-200	-10	30											2SC512 ヒコンプリ	
★ " 513	"	"	"	-50	-5	-1A	800	150	-1	-30																2SC513 ヒコンプリ	
" 514																											
" 515																											
" 516	東 芝	RF, PA	Si, DB	-80	-5	-1.5A	800	175	-0.5	-30	60	-2	-200	-5	200	60											84B
★ " 516A	"	"	"	-120	-5	-1.5A	800	175	-0.5	-30	60	-2	-200	-5	200	60											84B
★ " 517	"	RF	Ge, D	-18	-0.5	-10	55	85	-12	-18				-6	1	60											12A
★ " 518	"	RF, Conv. Mix Osc	"	-18	-0.5	-10	55	85	-12	-18				-6	1	60											12A
" 519																											
" 520																											
" 521																											
" 522	東 芝 富士通	RF	Si, EP	-25	-5	-100	250	175	-0.1	-15	30~120	-1	-10	-10	10	50											49C
" 522A	"	"	"	-50	-5	-100	250	175	-0.1	-15	30~120	-1	-10	-10	10	50											49C
" 523	富士通	RF, PA	"	-40	-5	-300	650	175	-0.1	-10	30~120	-10	-10	-10	10	60											84B
" 523A	"	"	"	-60	-5	-300	650	175	-0.1	-10	30~120	-10	-10	-10	10	60											84B
" 524	"	"	"	-25	-3	-100	350	175	-0.1	-10				-10	10	50											49C
★ " 525	東 芝	RF, Conv. Mix Osc	Ge, EMe	-20		-5	75	85	-10	-12				-6	1	20											48C
★ " 526	ソニー	PA	Si, E	-50	-5	-1A	500	150	-5	-50	70	-2	-100	-6	1	50											84C
★ " 527	"	"	"	-50	-5	-2A	5 W (T _c =25°C)	150	-5	-50	50	-2	-200	-6	1	50											97C
★ " 528	"	"	"	-50	-5	-2A	5 W (T _c =25°C)	150	-5	-50	70	-2	-100	-6	1	50											97C
★ " 529	"	RF, PA	Si, EMe	-50	-5	-1A	5 W (T _c =25°C)	150	-5	-50	80	-2	-100	-10	50												181
★ " 530	日 立	SW	Si, E	-50	-5	-100	200	175	-1	-20	35~200	-1	-10	-10	20												49C
★ " 531																											
★ " 532	三 洋	RF, PA	Si, TP	-50	-5	-200	500	150	-10	-40	80	-6		-6	10												84B
" 533																											
" 534																											
" 535	三 洋			-75	-4	-700	500	150			60	-6	-50														2SC873 2SC874 ヒコンプリ
" 536	"			-50	-4	-700	500	150			60	-6	-50														"
★ " 537	日 立	SW	Si, EP	-60	-5	-700	750	200	-1	-30	30~160	-4	-50	-10	20												2SC708 ヒコンプリ